

CLAIMS

What is claimed is:

1. A semiconductor device assembly, comprising:
a first semiconductor device;
discrete conductive elements extending over portions of an active surface of said first semiconductor device; and
a second semiconductor device positioned at least partially over said first semiconductor device and resting upon said discrete conductive elements in electrical isolation therefrom.
2. The semiconductor device assembly of claim 1, further comprising a substrate to which said first semiconductor device is secured.
3. The semiconductor device assembly of claim 2, wherein said substrate comprises at least one of a circuit board, an interposer, another semiconductor device, and leads.
4. The semiconductor device assembly of claim 1, wherein said discrete conductive elements comprise at least one of bond wires, tape-automated bond elements, and thermocompression bonded leads.
5. The semiconductor device assembly of claim 1, further comprising:
a dielectric coating on at least portions of said discrete conductive elements and electrically isolating at least said portions of said discrete conductive elements from a back side of said second semiconductor device.
6. The semiconductor device assembly of claim 5, wherein said dielectric coating comprises at least one of a nonconductive oxide and a polymer.

at least one second semiconductor device positioned at least partially over said first semiconductor device, a back side of said at least a second semiconductor device contacting and electrically isolated from said discrete conductive elements.

14. The multi-chip module of claim 13, further comprising:
an adhesive element positioned between said first semiconductor device and said at least a second semiconductor device.

15. The multi-chip module of claim 14, wherein said adhesive element substantially laterally surrounds at least portions of said discrete conductive elements located between said first semiconductor device and said second semiconductor device.

16. The multi-chip module of claim 13, further comprising:
a dielectric coating on at least portions of said discrete conductive elements in contact with said backside of said at least one second semiconductor device.

17. The multi-chip module of claim 13, further comprising:
a dielectric coating on at least portions of said back side of said at least one second semiconductor device in contact with said discrete conductive elements.

18. The multi-chip module of claim 13, wherein said substrate comprises at least one of a circuit board, an interposer, another semiconductor device, and leads.

19. The multi-chip module of claim 13, wherein said discrete conductive elements comprise at least one of bond wires, tape-automated bond elements, and thermocompression bonded leads.

20. The multi-chip module of claim 13, wherein each of said discrete conductive elements comprises a lead.

21. The multi-chip module of claim 13, further comprising:
an encapsulant material surrounding at least portions of said first semiconductor device and said
at least a second semiconductor device.

22. The multi-chip module of claim 13, further comprising:
external connective elements on said substrate coupled to said contact areas.

23. A method for assembling semiconductor devices, comprising:
providing a first semiconductor device;
placing discrete conductive elements over portions of said first semiconductor device; and
positioning a second semiconductor device at least partially over said first semiconductor device
and contacting at least some of said discrete conductive elements with a back side of said
second semiconductor device.

24. The method of claim 23, wherein said positioning said second semiconductor
device comprises positioning said second semiconductor device on said at least some of said
discrete conductive elements with said back side and said discrete conductive elements in mutual
electrical isolation.

25. The method of claim 24, further comprising:
providing a dielectric coating on at least portions of said discrete conductive elements.

26. The method of claim 25, wherein said providing comprises forming at least one of
a dielectric oxide and a dielectric polymer coating on at least said portions of said discrete
conductive elements.

27. The method of claim 24, further comprising:
forming a dielectric layer on at least portions of said back side.

45. A method for assembling semiconductor devices in a stacked arrangement with the stacked arrangement having a height substantially equal to combined thicknesses of each of the semiconductor devices and distances discrete conductive elements associated therewith protrude above each semiconductor device, comprising:

providing a first semiconductor device with discrete conductive elements protruding from an active surface thereof; and

positioning a second semiconductor device at least partially over said first semiconductor device and on at least some of said discrete conductive elements.

46. The method of claim 45, wherein said positioning comprises positioning said second semiconductor device on said at least some of said discrete conductive elements with a back side of said second semiconductor device electrically isolated from said discrete conductive elements.

47. The method of claim 46, further comprising:
providing a dielectric coating on at least portions of said at least some of said discrete conductive elements.

48. The method of claim 46, further comprising:
forming a dielectric coating on at least portions of said back side.

49. The method of claim 45, further comprising:
applying a quantity of adhesive material at least to said active surface of said first semiconductor device.

50. The method of claim 49, further comprising:
drawing said second semiconductor device toward said first semiconductor device.

51. The method of claim 50, wherein said drawing is effected by at least one of capillary action of said adhesive material, curing of said adhesive material, application of heat to said adhesive material, and vibration of said adhesive material.

52. The method of claim 49, wherein said applying is effected before said positioning.

53. The method of claim 49, wherein said applying is effected after said positioning.

54. The method of claim 53, further comprising:
drawing said second semiconductor device toward said first semiconductor device.

55. The method of claim 54, wherein said drawing is effected during curing of said adhesive material.

56. The method of claim 49, further comprising:
biasing at least one of said first and second semiconductor devices toward the other of said first and second semiconductor devices.

57. The method of claim 56, further comprising:
controlling said biasing.

58. The method of claim 57, wherein said controlling said biasing comprises
controlling biasing force to a level insufficient to deform, kink, bend, or collapse said discrete conductive elements.

59. The method of claim 45, further comprising:
positioning said first semiconductor device relative to a substrate.

60. The method of claim 59, further comprising:

connecting said discrete conductive elements to corresponding contact areas of said substrate.

61. The method of claim 59, further comprising:
establishing electrical communication between bond pads of said second semiconductor device
and corresponding contact areas of said substrate.

62. The method of claim 61, wherein said establishing communication comprises:
placing additional discrete conductive elements between each of said bond pads and a
corresponding contact area of said corresponding contact areas.

63. The method of claim 46, further comprising:
providing at least one external connective element in communication with at least one bond pad of
each of said first and second semiconductor devices.

64. The method of claim 63, further comprising:
encapsulating at least portions of said first and second semiconductor devices.

65. A semiconductor device assembly, comprising at least two semiconductor devices
in a stacked arrangement, said stacked arrangement having a height substantially equal to
combined thicknesses of said at least two semiconductor devices and distances discrete
conductive elements associated therewith protrude above each semiconductor device of said at
least two semiconductor devices.

66. The semiconductor device assembly of claim 65, wherein said discrete conductive
elements comprise bond wires.

67. The semiconductor device assembly of claim 65, wherein a back side of each upper
semiconductor device of said at least two semiconductor devices rests upon upper portions of
discrete conductive elements protruding above a surface of a next lower semiconductor device of
said at least two semiconductor devices.

68. The semiconductor device assembly of claim 65, further comprising:
a substrate to which at least one semiconductor device of said at least two semiconductor devices
is secured, said height of said stacked arrangement including a thickness of said substrate.

69. The semiconductor device assembly of claim 35, further comprising:
a protective encapsulant surrounding portions of at least one of said at least two semiconductor
devices, said height of said stacked arrangement including a thickness of said protective
encapsulant over a surface of at least one of said at least two semiconductor devices.